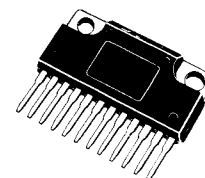




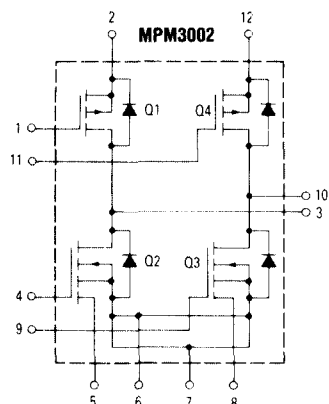
TMOS Power MOSFETs

Multiple Chip Products

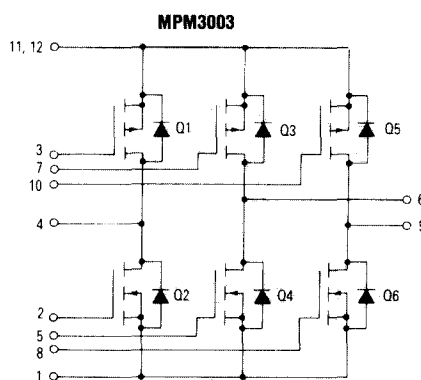


CASE 806-02

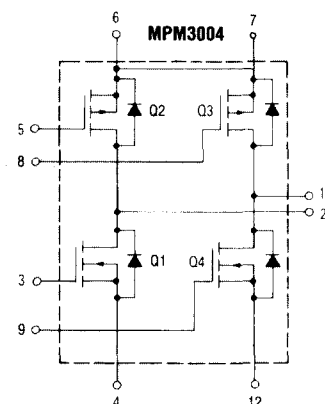
Table 17 — Multiple Chip Products in the Isolated ICePAK



H-Bridge with Current Sensing
100 Volts and 8 Amperes
P-Channel MOSFETs — $r_{DS(on)}$ = 0.4 Ohms Max
N-Channel SENSEFETs — $r_{DS(on)}$ = 0.15 Ohms Max



Three-Phase Bridge with Complementary Outputs
60 Volts and 10 Amperes
P-Channel — $r_{DS(on)}$ = 0.28 Ohms Max
N-Channel — $r_{DS(on)}$ = 0.15 Ohms Max



H-Bridge
60 Volts and 10 Amperes
P-Channel MOSFETs — $r_{DS(on)}$ = 0.28 Ohms Max
N-Channel MOSFETs — $r_{DS(on)}$ = 0.15 Ohms Max

Table 18 — TMOS Power MOSFET Modules

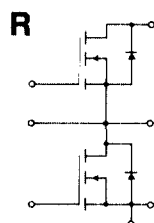
Max ID (cont) Amps	Max VDSS Volts	Device Type	Module Type	Max VDS(on) Volts	Conditions		Max. Resistive Switching					PD TC = 25°C Watts	Case No.	Circuit Config
					ID Amps	VGS Volts	ton µs	toff µs	tf µs	Conditions				
										ID(A)	VG			
15	450	MT15FR45	UL Six-pack	6	15x6	10	0.6	2	0.5	15	10	125x6	809-01	R
50	450	MT50BY45	Dual	7	50	10	0.8	1.3	0.2	50	10	400x2	816-01	Y

Table 19 — IGBT Power Modules

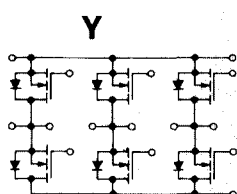
UL
RECOGNIZED

Max I _C (cont) Amps	Max V _{CES} Volts	Device Type	Module Type	Max V _{CE} Volts	Conditions		Max. Resistive Switching					P _D T _C = 25°C Watts	Case No.	Circuit Config	
					I _C Amps	V _{GE} Volts	t _{on} μs	t _s μs	t _f μs	Conditions					
											I _C (A)	V _G (V)			
25	1000	MG25BZ100	UL Dual	5	25	15	1	2	1		25	15	200x2	813-01	Z
50	1000	MG50BZ100	UL Dual	5	50	15	1	1.5	1		50	15	300x2	813-01	Z
100	1000	MG100BZ100	UL Dual	5	100	15	1	1.5	1		100	15	400x2	814B-01	Z
25	500	MG25BZ50	Dual	5	25	15	1	1.5	1		25	15	125x2	813-01	Z
50	500	MG50BZ50	Dual	5	50	15	1	1.5	1		50	15	300x2	813-01	Z
75	500	MG75BZ50	Dual	5	75	15	1	1.5	1		75	15	350x2	813-01	Z
100	500	MG100BZ50	Dual	5	100	15	1	1.5	1		100	15	400x2	813-01	Z

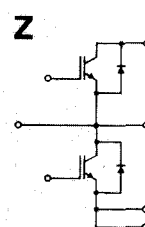
Table 20 — TMOS Power MOSFET and IGBT Power Module Circuit Configurations and Packages



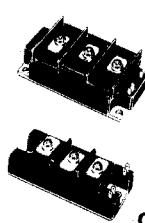
CASE 816-01



CASE 809-01



CASE 814B-01



CASE 813-01